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APPLICATION NO.	FILING DATE	FIRST NAMED INVENTOR	ATTORNEY DOCKET NO.	CONFIRMATION NO.
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09/787,038

03/13/2001

Jun-ichiro Furihata

108868

8734

25944

7590

03/24/2003

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EXAMINER

LATTIN, CHRISTOPHER W

ART UNIT

PAPER NUMBER

2812

DATE MAILED: 03/24/2003

8

Please find below and/or attached an Office communication concerning this application or proceeding.

Office Action Summary

Application No.

09/787,038

Applicant(s)

FURIHATA ET AL.

Examiner

Christopher W Lattin

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-- The MAILING DATE of this communication appears on the cover sheet with the correspondence address --

Period for Reply

A SHORTENED STATUTORY PERIOD FOR REPLY IS SET TO EXPIRE 3 MONTH(S) FROM THE MAILING DATE OF THIS COMMUNICATION.

- Extensions of time may be available under the provisions of 37 CFR 1.136(a). In no event, however, may a reply be timely filed after SIX (6) MONTHS from the mailing date of this communication.
- If the period for reply specified above is less than thirty (30) days, a reply within the statutory minimum of thirty (30) days will be considered timely.
- If NO period for reply is specified above, the maximum statutory period will apply and will expire SIX (6) MONTHS from the mailing date of this communication.
- Failure to reply within the set or extended period for reply will, by statute, cause the application to become ABANDONED (35 U.S.C. § 133).
- Any reply received by the Office later than three months after the mailing date of this communication, even if timely filed, may reduce any earned patent term adjustment. See 37 CFR 1.704(b).

Status

- 1) ☐ Responsive to communication(s) filed on ____.
- 2a) ☐ This action is **FINAL**. 2b) ☒ This action is non-final.
- 3) ☐ Since this application is in condition for allowance except for formal matters, prosecution as to the merits is closed in accordance with the practice under *Ex parte Quayle*, 1935 C.D. 11, 453 O.G. 213.

Disposition of Claims

- 4) ☒ Claim(s) 17-34 is/are pending in the application.
- 4a) Of the above claim(s) ____ is/are withdrawn from consideration.
- 5) ☐ Claim(s) ____ is/are allowed.
- 6) ☒ Claim(s) 17-34 is/are rejected.
- 7) ☐ Claim(s) ____ is/are objected to.
- 8) ☐ Claim(s) ____ are subject to restriction and/or election requirement.

Application Papers

- 9) ☐ The specification is objected to by the Examiner.
- 10) ☐ The drawing(s) filed on ____ is/are: a) ☐ accepted or b) ☐ objected to by the Examiner.
- Applicant may not request that any objection to the drawing(s) be held in abeyance. See 37 CFR 1.85(a).
- 11) ☐ The proposed drawing correction filed on ____ is: a) ☐ approved b) ☐ disapproved by the Examiner.
- If approved, corrected drawings are required in reply to this Office action.
- 12) ☐ The oath or declaration is objected to by the Examiner.

Priority under 35 U.S.C. §§ 119 and 120

- 13) ☒ Acknowledgment is made of a claim for foreign priority under 35 U.S.C. § 119(a)-(d) or (f).
- a) ☒ All b) ☐ Some * c) ☐ None of:
- ☐ Certified copies of the priority documents have been received.
 - ☐ Certified copies of the priority documents have been received in Application No. ____.
 - ☒ Copies of the certified copies of the priority documents have been received in this National Stage application from the International Bureau (PCT Rule 17.2(a)).
- * See the attached detailed Office action for a list of the certified copies not received.
- 14) ☐ Acknowledgment is made of a claim for domestic priority under 35 U.S.C. § 119(e) (to a provisional application).
- a) ☐ The translation of the foreign language provisional application has been received.
- 15) ☐ Acknowledgment is made of a claim for domestic priority under 35 U.S.C. §§ 120 and/or 121.

Attachment(s)

- ☐ Notice of References Cited (PTO-892)
- ☐ Notice of Draftsperson's Patent Drawing Review (PTO-948)
- ☒ Information Disclosure Statement(s) (PTO-1449) Paper No(s) 4.
- ☐ Interview Summary (PTO-413) Paper No(s) ____.
- ☐ Notice of Informal Patent Application (PTO-152)
- ☐ Other:

DETAILED ACTION

Claim Rejections - 35 USC § 103

The following is a quotation of 35 U.S.C. 103(a) which forms the basis for all obviousness rejections set forth in this Office action:

(a) A patent may not be obtained though the invention is not identically disclosed or described as set forth in section 102 of this title, if the differences between the subject matter sought to be patented and the prior art are such that the subject matter as a whole would have been obvious at the time the invention was made to a person having ordinary skill in the art to which said subject matter pertains. Patentability shall not be negated by the manner in which the invention was made.

Claims 17-20, 22, 24-31 and 34 are rejected under 35 U.S.C. 103(a) as being unpatentable over Furukawa (U.S. Patent 5,932,048) in view of Kai et al. (U.S. Patent 5,899,731).

Furukawa teaches a method of forming a bonded wafer by slicing a single crystal silicon wafer from an ingot, but fails to teach the steps taken prior to bonding namely subjecting the wafer to chamfering, lapping, etching using of an alkali and acid etch, mirror polishing, and cleaning. Kai et al. teach a method of lapping, etching using a alkali etch solution and then acid washing with and acid etch solution, mirror polishing the wafer, and cleaning. See column 2 lines 8-12, column 3 lines 1-39, and claims 1-3.

Claims 21, 23, 32 and 33 are rejected under 35 U.S.C. 103(a) as being unpatentable over Furukawa (U.S. Patent 5,932,048) in view of Kai et al. (U.S. Patent 5,899,731) as applied to claim 17 above and further in view of Miyazaki (U.S. Patent 5,976,983).

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Furukawa in view of Kai et al. is applied supra and when taken together teach a method of forming a bonded wafer by slicing a single crystal silicon wafer from an ingot, subjecting the wafer to chamfering, lapping, etching using of an alkali and acid etch, mirror polishing, and cleaning and then bonding wafers together, but fail to teach the claimed etching amounts. Miyazaki et al. teach a similar method of wafer preparation to Kai et al. but further specify using an alkaline solution to etch 0.1-30 microns followed by an acid solution to etch 15-50 microns. It would have been obvious to one skilled in the art at the time of the invention to etch the amounts specified by Miyazaki et al. in order to obtain a smooth flat surface. Given that the method of formation of the claimed devices is obviated, claims 32 and 33, which refer to the final characteristics, are also obviated.


Conclusion

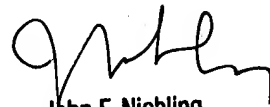
Any inquiry concerning this communication or earlier communications from the examiner should be directed to Christopher Lattin whose telephone number is (703) 305-3017. The examiner can normally be reached Monday through Friday from 8:00 A.M. to 5:00 P.M.

If attempts to reach the examiner by telephone are unsuccessful, the examiner's supervisor, John Niebling, can be reached at (703) 308-3325. The fax numbers for this Group are (703) 872-9318 for responses to non-final actions and (703) 872-9319 responses to final actions.

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Any inquiry of a general nature or relating to the status of this application or proceeding should be directed to the Group receptionist whose telephone number is (703) 308-0956.

CWL 
March 20, 2003


John F. Niebling
Supervisory Patent Examiner
Technology Center 2800